L Numb r	Hits	Search T xt	DB	Time stamp
•	680	(345/30,55,84).ccls.	USPAT;	2003/02/13
			US-PGPUB	18:12
-	3	("5061049" "5583688" "6147790").pn.	USPAT;	2003/02/13
			US-PGPUB	18:16
•	2691	(mems r microelectr mechanical or (micr	USPAT;	2003/02/13
		adj electro adj mechanical)) and (mirror or	US-PGPUB;	18:19
		reflect\$3)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	3369	(mems or microelectromechanical or (micro	USPAT;	2003/02/13
		adj electro adj mechanical)) and (mirror or	US-PGPUB;	18:20
		reflect\$3 or deflect\$3)	EPO; JPO;	1 1
			DERWENT;	
			IBM_TDB	
-	0	((mems or microelectromechanical or (micro	USPAT;	2003/02/13
		adj electro adj mechanical)) and (mirror or	US-PGPUB;	18:20
	1	reflect\$3 or deflect\$3)) and (semicoduct\$3	EPO; JPO;	
		with substrate)	DERWENT;	
		will data and a second a second and a second a second and	IBM_TDB	
_	734	((mems or microelectromechanical or (micro	USPAT;	2003/02/13
	/ / /	adj electro adj mechanical)) and (mirror or	US-PGPUB;	18:20
		reflect\$3 or deflect\$3)) and (semiconduct\$3	EPO; JPO;	10.20
			DERWENT;	
		with substrate)	IBM_TDB	<u> </u>
	420	///www.armiaradactromachanical or	USPAT;	2003/02/13
•	120	(((mems or microelectromechanical or	· ·	18:21
		(micro adj electro adj mechanical)) and	US-PGPUB;	10:21
		(mirror or reflect\$3 or deflect\$3)) and	EPO; JPO; DERWENT;	! 
		(semiconduct\$3 with substrate)) and	,	
		torsion\$2	IBM_TDB	0000/00/43
•	3	(((((mems or microelectromechanical or	USPAT;	2003/02/13 18:21
		(micro adj electro adj mechanical)) and	US-PGPUB;	10:21
		(mirror or reflect\$3 or deflect\$3)) and	EPO; JPO;	
		(semiconduct\$3 with substrate)) and	DERWENT;	
		torsion\$2) and (switch\$3 same voltage)) and	IBM_TDB	
		(memory same stor\$3)		0000/00/40
•	1711	(359/223,224,290-292,298).ccls.	USPAT;	2003/02/13
		(345/85).ccls.	US-PGPUB	18:25
•	29	((((mems or microelectromechanical or	USPAT;	2003/02/14
		(micro adj electro adj mechanical)) and	US-PGPUB;	12:28
		(mirror or reflect\$3 or deflect\$3)) and	EPO; JPO;	:
		(semiconduct\$3 with substrate)) and	DERWENT;	1
		torsion\$2) and (switch\$3 same voltage)	IBM_TDB	1
-	6262	(mems or microelectromechanical or (micro	USPAT;	2003/02/14
		adj electro adj mechanical))	US-PGPUB;	13:44
			EPO; JPO;	
		 	DERWENT;	
			IBM_TDB	1
-	1128	((mems or microelectromechanical or (micro	USPAT;	2003/02/14
		adj electr adj m chanical)) ) and	US-PGPUB;	13:43
		semiconduct\$3 n ar5 substrate	EPO; JPO;	
			DERWENT;	
		•	IBM_TDB	I L

•	114	(((mems or microelectromechanical or	USPAT;	2003/02/14
		(micro adj   ctro adj m chanical)) ) and semiconduct\$3 n ar5 substrate) and torsion\$2	US-PGPUB; EPO; JPO; DERWENT;	12:29
			IBM_TDB	
-	38	((((m ms or micro lectrom chanical or	USPAT;	2003/02/14
		(micr adj el ctro adj mechanical)) ) and	US-PGPUB;	12:30
		semiconduct\$3 near5 substrate) and	EPO; JPO;	
		torsion\$2) and (driv\$3 with voltage)	DERWENT; IBM_TDB	
•	12	(((((mems or microelectromechanical or	USPAT;	2003/02/14
	100	(micro adj electro adj mechanical)) ) and	US-PGPUB;	12:35
		semiconduct\$3 near5 substrate) and	EPO; JPO;	
		torsion\$2) and (driv\$3 with voltage)) and memory	DERWENT; IBM_TDB	
-	23	(((((mems or microelectromechanical or	USPAT;	2003/02/14
		(micro adj electro adj mechanical)) ) and	US-PGPUB;	12:35
		semiconduct\$3 near5 substrate) and	EPO; JPO;	
		torsion\$2) and memory) not ((((((mems or	DERWENT;	
		microelectromechanical or (micro adj electro adj mechanical)) ) and	IBM_TDB	
		semiconduct\$3 near5 substrate) and torsion\$2) and (driv\$3 with voltage)) and		
		memory)		
	115	((mems or microelectromechanical or (micro	USPAT;	2003/02/14
		adj electro adj mechanical)) ) and (memory	US-PGPUB;	13:04
		same capacitor\$1)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
•	6262	(mems or microelectromechanical or (micro	USPAT;	2003/02/14
		adj electro adj mechanical))	US-PGPUB;	13:03
			EPO; JPO; DERWENT;	
			IBM_TDB	
_	115	((mems or microelectromechanical or (micro	USPAT;	2003/02/14
	1.5	adj electro adj mechanical)) ) and (memory	US-PGPUB;	13:39
		same capacitor\$1)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	7	(US-5905571-\$ or US-6518609-\$ or	USPAT;	2003/02/14
		US-6473361-\$ or US-6312134-\$ or	US-PGPUB	13:38
		US-6242989-\$ or US-5867302-\$).did. or		
		(US-20020149834-\$).did.		
	1	US-20020076138-A1.DID. and ((mems or	USPAT;	2003/02/14
		microelectromechanical or (micro adj	US-PGPUB	13:38
	1	electro adj mechanical)) )		
	7	((US-5905571-\$ or US-6518609-\$ or	USPAT;	2003/02/14
	i	US-6473361-\$ or US-6312134-\$ or	US-PGPUB	13:38
		US-6242989-\$ r US-5867302-\$).did. or		
		(US-20020149834-\$).did.) and ((mems r		
		micr electr mechanical r (micr adj		
	1	electro adj mechanical)) )	<u>.                                    </u>	

-	3	(((US-5905571-\$ r US-6518609-\$ r	USPAT;	2003/02/14
		US-6473361-\$ or US-6312134-\$ r	US-PGPUB	13:38
1		US-6242989-\$ or US-5867302-\$).did. or		
		(US-20020149834-\$).did.) and ((mems or	!	
		micr electr m chanical r (micr adj		
1		I ctro adj m chanical)) )) and (((m ms or		
1		micr electromechanical or (micro adj		
		electro adj mechanical)) ) and		
		semiconduct\$3 near5 substrate)		
-	4	(((US-5905571-\$ or US-6518609-\$ or	USPAT;	2003/02/14
		US-6473361-\$ or US-6312134-\$ or	US-PGPUB;	13:40
		US-6242989-\$ or US-5867302-\$).did. or	EPO; JPO;	10.40
		(US-20020149834-\$).did.) and ((mems or	DERWENT;	
		microelectromechanical or (micro adj	IBM_TDB	
		electro adj mechanical)) )) and torsion\$2	15111_175	
-	3580	(micro adj mirror) or micromirror	USPAT;	2003/02/14
			US-PGPUB;	13:40
	- 6		EPO; JPO;	10.70
			DERWENT;	
			IBM_TDB	
-	3073	((micro adj mirror) or micromirror) not	USPAT;	2003/02/19
Ì	33.3	((mems or microelectromechanical or (micro	US-PGPUB;	14:56
i		adj electro adj mechanical)) )	EPO; JPO;	14:50
			DERWENT;	
			1	•
_	1711	(((micro adj mirror) or micromirror) not	IBM_TDB	2002/02/4
	.,,,		USPAT;	2003/02/14
		((mems or microelectromechanical or (micro adj electro adj mechanical)) )) and (actuat\$3	US-PGPUB;	13:42
		or torsion\$2 or driv\$3)	EPO; JPO;	
		or torsion \$2 or arry \$5)	DERWENT;	
	25	///miero odi mirror) or miero mirror) a st	IBM_TDB	0000/00/4
_	25	((((micro adj mirror) or micromirror) not	USPAT;	2003/02/14
		((mems or microelectromechanical or (micro	US-PGPUB;	13:46
		adj electro adj mechanical)) )) and (actuat\$3	EPO; JPO;	
		or torsion\$2 or driv\$3)) and (memory same	DERWENT;	
	173	capacitor\$1)	IBM_TDB	0000/2011
-	1/3	((((micro adj mirror) or micromirror) not	USPAT;	2003/02/14
		((mems or microelectromechanical or (micro	US-PGPUB;	13:43
		adj electro adj mechanical)) )) and (actuat\$3	EPO; JPO;	
		or torsion\$2 or driv\$3)) and semiconduct\$3	DERWENT;	
	20	near5 substrate	IBM_TDB	
•	30	((((US-5905571-\$ or US-6518609-\$ or	USPAT;	2003/02/14
		US-6473361-\$ or US-6312134-\$ or	US-PGPUB;	13:44
		US-6242989-\$ or US-5867302-\$).did. or	EPO; JPO;	
		(US-20020149834-\$).did.) and ((mems or	DERWENT;	
		microelectromechanical or (micro adj	IBM_TDB	
		electro adj mechanical)))) and (memory		
		same capacitor\$1)) (((((micro adj mirror) or		
		micromirror) not ((mems or		
		micro lectr mechanical r (micr adj	!	
		electro adj mechanical)) )) and (actuat\$3 or		
		torsi n\$2 r driv\$3)) and (m m ry same		
		capacit r\$1))		

	3/02/14
US-6473361-\$ r US-6312134-\$ or US-PGPUB; 13:4	5
US-6242989-\$ or US-5867302-\$).did. r EPO; JPO;	
(US-20020149834-\$).did.) and ((mems r DERWENT;	
microelectr mechanical r (micr adj IBM_TDB	
electr adj mechanical)) )) and t rsi n\$2)	
((((((micr adj mirror) or micromirr r) not	
((mems or microelectromechanical or (micro	
adj electro adj mechanical)) )) and (actuat\$3	
or torsion\$2 or driv\$3)) and semiconduct\$3	
near5 substrate) and torsion\$2)	
- 63 (((((micro adj mirror) or micromirror) not USPAT; 2003	3/02/14
((mems or microelectromechanical or (micro US-PGPUB; 13:4	5
adj electro adj mechanical)) )) and (actuat\$3	
or torsion\$2 or driv\$3)) and semiconduct\$3 DERWENT;	
near5 substrate) and torsion\$2 IBM_TDB	
- 67 (((((US-5905571-\$ or US-6518609-\$ or USPAT; 2003	3/02/14
US-6473361-\$ or US-6312134-\$ or US-PGPUB; 13:4	5
US-6242989-\$ or US-5867302-\$).did. or EPO; JPO;	
(US-20020149834-\$).did.) and ((mems or DERWENT;	
microelectromechanical or (micro adj IBM_TDB	
electro adj mechanical)) )) and torsion\$2)	
((((((micro adj mirror) or micromirror) not	
((mems or microelectromechanical or (micro	
adj electro adj mechanical)) )) and (actuat\$3	
or torsion\$2 or driv\$3)) and semiconduct\$3	
near5 substrate) and torsion\$2)) (((((micro	
adj mirror) or micromirror) not ((mems or	
microelectromechanical or (micro adj	
electro adj mechanical)) )) and (actuat\$3 or	
torsion\$2 or driv\$3)) and semiconduct\$3	
near5 substrate) and torsion\$2)	
- 4025 "67" and (memory same capacitor\$1) USPAT; 2003	/02/14
US-PGPUB; 14:19	9
EPO; JPO;	
DERWENT;	:
IBM_TDB	
- 10 ((((((US-5905571-\$ or US-6518609-\$ or USPAT; 2003	/02/14
US-6473361-\$ or US-6312134-\$ or US-PGPUB; 13:5	2
US-6242989-\$ or US-5867302-\$).did. or EPO; JPO;	İ
(US-20020149834-\$).did.) and ((mems or DERWENT;	
microelectromechanical or (micro adj IBM_TDB	
electro adj mechanical)) )) and torsion\$2)	
((((((micro adj mirror) or micromirror) not	
((mems or microelectromechanical or (micro	
adj electro adj mechanical)) )) and (actuat\$3	
or torsion\$2 or driv\$3)) and semiconduct\$3	-
near5 substrate) and torsion\$2)) (((((micro	
adj mirr r) or micr mirr r) n t ((m ms r	
micr electromechanical or (mi r adj	
lectr adj mechanical)) )) and (actuat\$3 r	
t rsi n\$2 or driv\$3)) and s mic nduct\$3	i
near5 substrate) and t rsi n\$2)) and	
(m m ry same capacit r\$1)	:

•	2	6266178.pn.	USPAT;	2003/02/14
			US-PGPUB;	13:52
			EPO; JPO;	
	}		DERWENT;	İ
	1	i	IBM_TDB	1
•	5	(US-6473361-\$ r US-6242989-\$ r	USPAT	2003/02/14
		US-5867302-\$ or US-6046840-\$ r		14:19
		US-6266178-\$).did.		<b>)</b>
•	5	((US-6473361-\$ or US-6242989-\$ or	USPAT;	2003/02/14
		US-5867302-\$ or US-6046840-\$ or	US-PGPUB;	16:08
		US-6266178-\$).did.) and (memory same	EPO; JPO;	
		capacitor\$1)	DERWENT;	
			IBM_TDB	
	9335	((mems or microelectromechanical or (micro	USPAT;	2003/02/14
		adj electro adj mechanical)) ) ((micro adj	US-PGPUB;	16:08
		mirror) or micromirror)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	55	(((mems or microelectromechanical or	USPAT;	2003/02/14
		(micro adj electro adj mechanical)) ) ((micro	US-PGPUB;	16:10
		adj mirror) or micromirror)) and ((memory	EPO; JPO;	
		adj cell) with driv\$3)	DERWENT;	
			IBM_TDB	
	67	(((mems or microelectromechanical or	USPAT;	2003/02/14
		(micro adj electro adj mechanical)) ) ((micro	US-PGPUB;	16:10
		adj mirror) or micromirror)) and ((memory	EPO; JPO;	
		adj cell\$1) with driv\$3)	DERWENT;	
			IBM_TDB	
- 6 K	5	(((US-5905571-\$ or US-6518609-\$ or	USPAT;	2003/02/19
		US-6473361-\$ or US-6312134-\$ or	US-PGPUB;	11:35
		US-6242989-\$ or US-5867302-\$).did. or	EPO; JPO;	
		(US-20020149834-\$).did.) and ((mems or	DERWENT;	
		microelectromechanical or (micro adj	IBM_TDB	
		electro adj mechanical)) )) and (memory		
		same capacitor\$1)		
	3	((((US-5905571-\$ or US-6518609-\$ or	USPAT;	2003/02/14
		US-6473361-\$ or US-6312134-\$ or	US-PGPUB;	17:15
		US-6242989-\$ or US-5867302-\$).did. or	EPO; JPO;	i
		(US-20020149834-\$).did.) and ((mems or	DERWENT;	
		microelectromechanical or (micro adj	IBM_TDB	
		electro adj mechanical)) )) and (memory		
		same capacitor\$1)) and (memory adj cell\$1)		
•	9370	((micro adj mirror) or micromirror) or ((mems	USPAT;	2003/02/19
		or microelectromechanical or (micro adj	US-PGPUB;	14:56
	lii -	electro adj mechanical)) )	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	251	(((micro adj mirror) or micromirror) or	USPAT;	2003/02/19
		((mems or micr el ctrom chani al r (micr	US-PGPUB;	15:09
	1	adj el ctr adj mechanical)) )) and (m mory	EPO; JPO;	
		adj2 cell)	DERWENT;	
			IBM_TDB	

•	12	(((micro adj mirror) or micromirror) or	USPAT;	2003/02/19
		((mems r micro I ctrom chanical or (micro	US-PGPUB;	14:57
		adj el ctr adj m chanical)) )) and ((memory	EPO; JPO;	
		adj2 cell) same capacitor\$1 same	DERWENT;	
		transistor\$1)	IBM_TDB	
-	12	((((micr adj mirror) r micromirr r) r	USPAT;	2003/02/19
		((mems or micr el ctr mechanical r (micro	US-PGPUB;	14:57
		adj electro adj mechanical)) )) and (memory	EPO; JPO;	1
		adj2 cell)) and ((memory adj2 cell) same	DERWENT;	
		capacitor\$1 same transistor\$1)	IBM_TDB	
•	44	((((micro adj mirror) or micromirror) or	USPAT;	2003/02/20
		((mems or microelectromechanical or (micro	US-PGPUB;	12:25
		adj electro adj mechanical)) )) and (memory	EPO; JPO;	
		adj2 cell)) and ground	DERWENT;	:
			IBM_TDB	
•	5	((((micro adj mirror) or micromirror) or	USPAT;	2003/02/20
		((mems or microelectromechanical or (micro	US-PGPUB;	12:52
		adj electro adj mechanical)) )) and (memory	EPO; JPO;	
		adj2 cell)) and (ground same reset\$4)	DERWENT;	
			IBM_TDB	
•	17	(((micro adj mirror) or micromirror) or	USPAT;	2003/02/20
		((mems or microelectromechanical or (micro	US-PGPUB;	12:53
		adj electro adj mechanical)))) and (pass adj	EPO; JPO;	]
		transistor)	DERWENT;	
			IBM_TDB	
	11	(((micro adj mirror) or micromirror) or	USPAT;	2003/02/20
		((mems or microelectromechanical or (micro	US-PGPUB;	12:58
		adj electro adj mechanical)))) and ((pass adj	EPO; JPO;	
		transistor) same capacitor)	DERWENT;	1
			IBM_TDB	j
	2	(((micro adj mirror) or micromirror) or	USPAT;	2003/02/20
		((mems or microelectromechanical or (micro	US-PGPUB;	13:00
		adj electro adj mechanical)))) and ((pass adj	EPO; JPO;	
		transistor) same capacitor same gate)	DERWENT;	]
		,	IBM_TDB	
	64	(((micro adj mirror) or micromirror) or	USPAT;	2003/02/20
		((mems or microelectromechanical or (micro	US-PGPUB;	13:00
		adj electro adj mechanical)))) and	EPO; JPO;	
		((transistor) same capacitor same gate) and	DERWENT;	
		ground\$3	IBM_TDB	
	37	(((micro adj mirror) or micromirror) or	USPAT;	2003/02/20
		((mems or microelectromechanical or (micro	US-PGPUB;	13:26
		adj electro adj mechanical)))) and	EPO; JPO;	
		((transistor) same capacitor same gate) and	DERWENT;	]
		(transistor same ground\$3)	IBM_TDB	İ
	2	5285407.pn.	USPAT;	2003/02/20
		· •	US-PGPUB;	13:26
			EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	1